

SILICON STEP RECOVERY DIODE

DESCRIPTION:

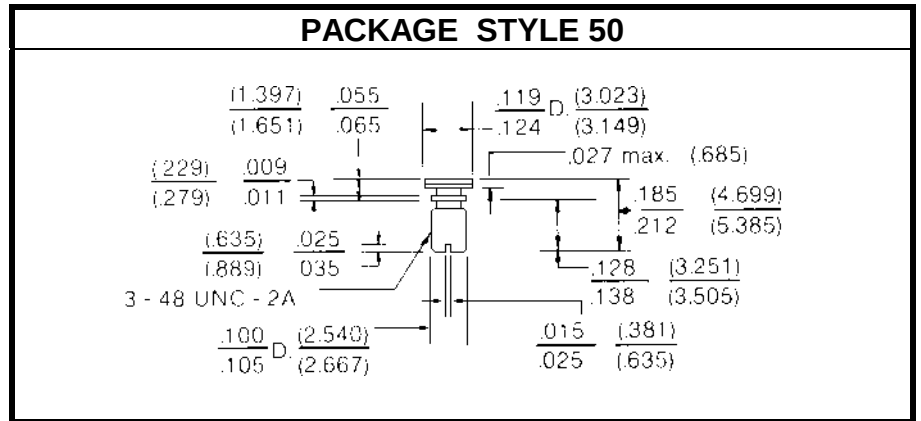
The **ASI MA43000** is a Silicon Step Recovery Diode.

FEATURES:

- Low Transition Time
- Tight Capacitance

MAXIMUM RATINGS

V	105 V
P_{DISS}	15 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	12 °C/W



CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
V_B	I _R = 10 μA	85		105	V
P_{OUT}	P _{IN} = 15 W F _{IN} = 333 MHz F _{OUT} = 2.0 GHz	4.0			W
C_j	V _R = 6.0 V f = 1.0 MHz	3.0		4.5	pF
T_L	I _F = 10 mA I _R = 6.0 mA	250		500	nS
T_S	V _R = 10 V I _F = 10 mA			600	pS